

1. General description:

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits:

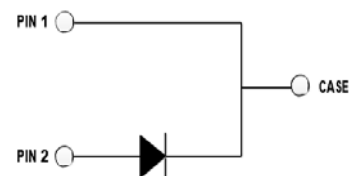
- Zero Reverse Recovery Current
- Positive temperature coefficient
- Temperature-independent performance
- High-speed switching
- Low switching loss
- Low heat dissipation requirements

3. Applications:

- Switching power supply
- Power factor correction
- Motor drive, traction
- Charging pile
- PC Silverbox

4. Typical Performance Diagrams and Package:

V_{RRM}	650	V
$I_F(135^{\circ}C)$	15	A
Q_c	34	nC



5. Ordering information:

Parts Number	Marking	Package	Vde min	IF max(A)	Pins	SPQ	Packaging
TSSiC065S012D	TSSiC065S012D	TO-220-2L	650V	12A	2	600	Tube

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6. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	Test Conditions
Reverse voltage (Repetitive peak)	V_{RRM}	650	V	$T_C = 25^\circ\text{C}$
Reverse Voltage (Surge peak)	V_{RSM}	650		$T_C = 25^\circ\text{C}$
Reverse voltage (DC)	V_{DC}	650		$T_C = 25^\circ\text{C}$
Continuous forward current	I_F	32	A	$T_C = 25^\circ\text{C}$
		15		$T_C = 135^\circ\text{C}$
		12		$T_C = 151^\circ\text{C}$
Surge non-repetitive forward current	I_{FSM}	96	A	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}, \text{half Sine Pulse}$
Total power dissipation	P_{TOT}	125	W	$T_C = 25^\circ\text{C}$
i^2t value	$\int i^2 dt$	46	A^2s	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$
Operating temperature	T_j	-55~175	$^\circ\text{C}$	
storage temperature	T_{stg}	-55~175	$^\circ\text{C}$	
Mounting Torque	M	1	Nm	M3 Screw

7. Thermal Characteristics

Parameter	Symbol	Values			Unit	Test Condition
		Min.	Typ.	Max.		
Thermal resistance	$R_{th(j-c)}$	/	1.2	/	$^\circ\text{C}/\text{W}$	

8. Electrical Characteristics $T_j = 25^\circ\text{C}$

Parameter	Symbol	Values			Unit	Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	/	/	V	$I_R = 100 \mu\text{A}$
Forward voltage	V_F	/	1.45	1.70	V	$I_F = 12\text{A}, T_j = 25^\circ\text{C}$
		/	1.75	2.50		$I_F = 12\text{A}, T_j = 175^\circ\text{C}$
Reverse current	I_R	/	1	35	μA	$V_R = 650\text{V}, T_j = 25^\circ\text{C}$
		/	5	220		$V_R = 650\text{V}, T_j = 175^\circ\text{C}$
Total capacitance	C	/	660	/	pF	$V_R = 0\text{V}, f = 1\text{MHz}$
		/	65	/		$V_R = 200\text{V}, f = 1\text{MHz}$
		/	54	/		$V_R = 400\text{V}, f = 1\text{MHz}$
Total capacitive charge	Q_C	/	34	/	nC	$V_R = 400\text{V}$
Capacitance Stored Energy	E_C	/	5.1	/	μJ	$V_R = 400\text{V}$

9. Typical Electrical Characteristics Curves

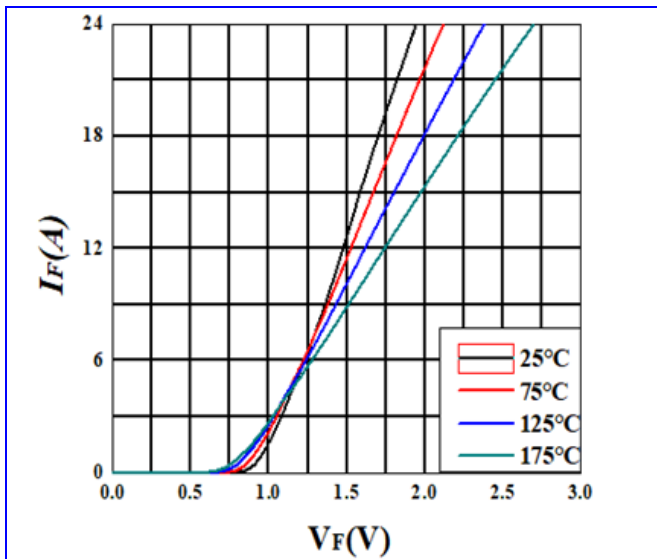


Figure 1. Forward Characteristics

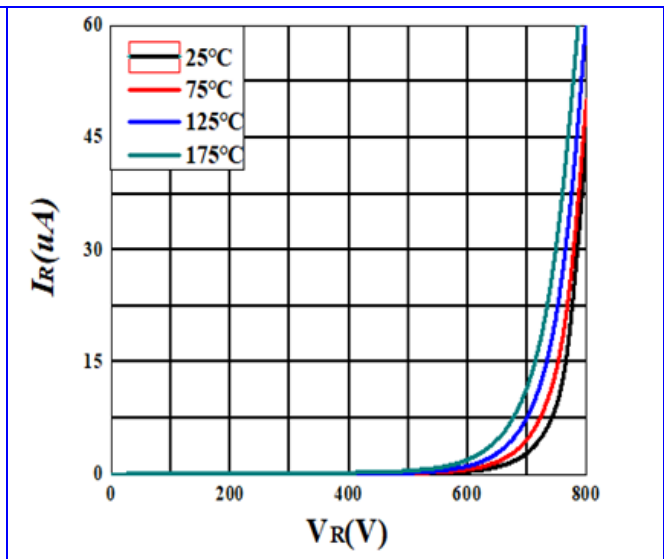


Figure 2. Reverse Characteristics

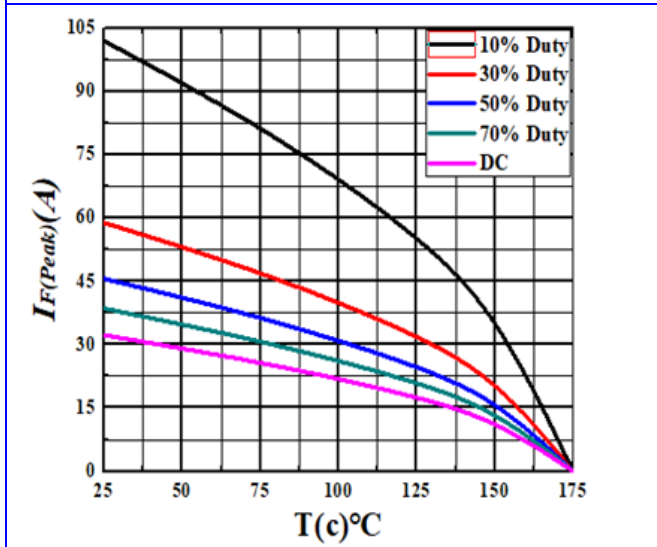


Figure 3. Current Derating

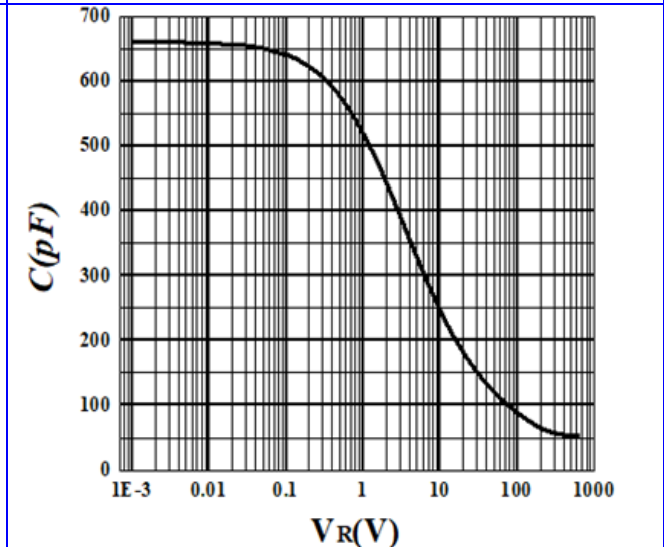


Figure 4. Capacitance vs. Reverse Voltage

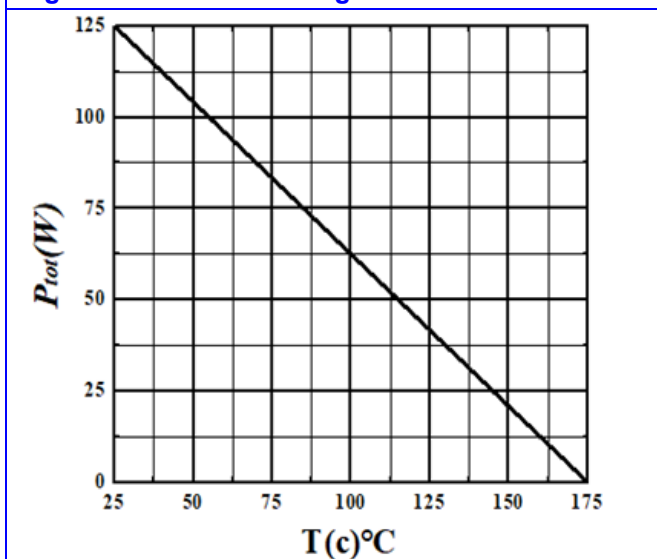


Figure 5. Power Derating

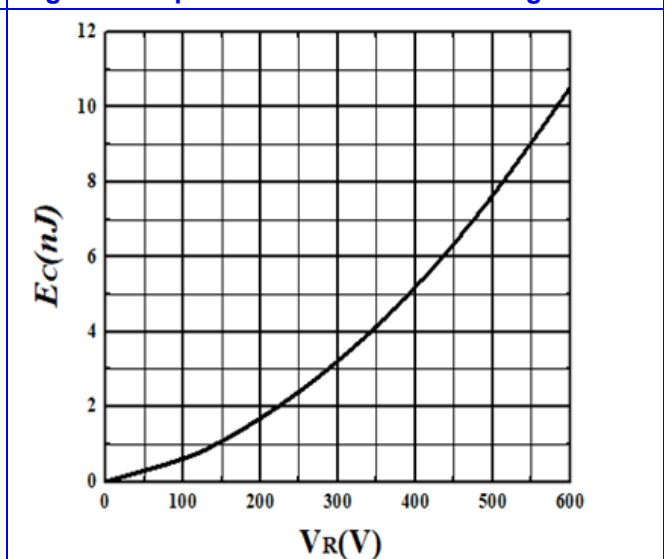


Figure 6. Capacitance Stored Energy

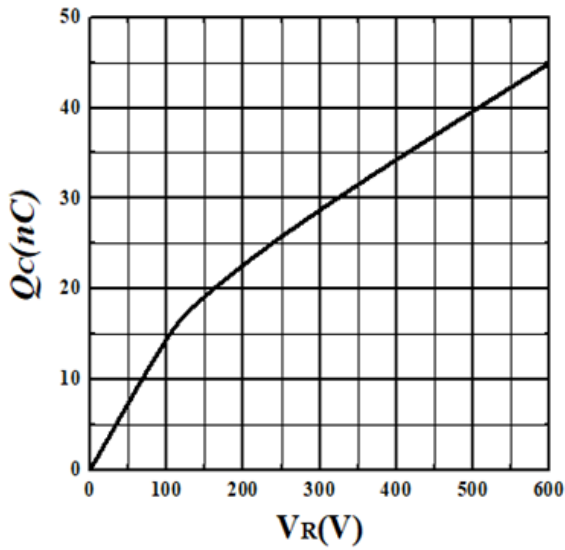
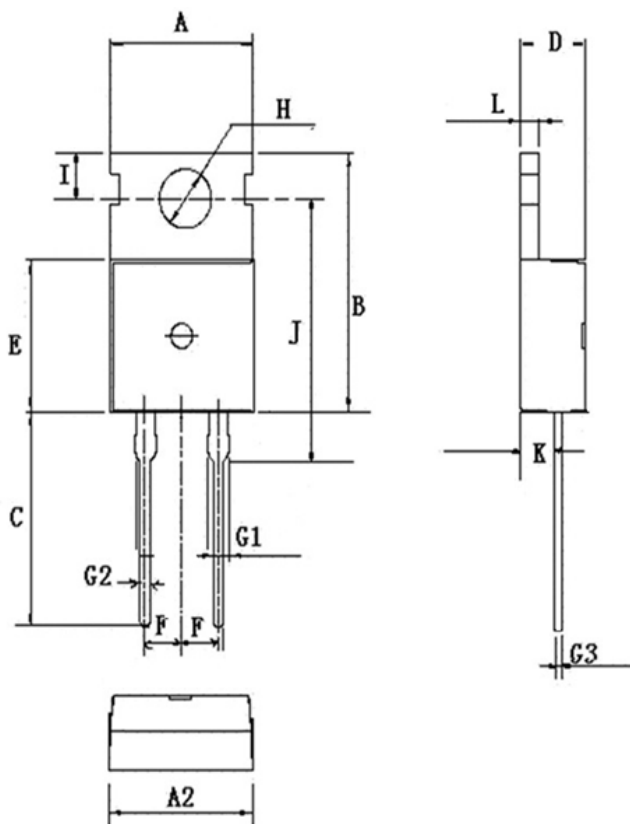


Figure 7. Total Capacitance Charge vs. Reverse Voltage

10. Package



SYMBOL	mm		
	MIN	NOM	MAX
A	9.66	9.90	10.28
A2	9.80	10.00	10.20
B	15.60	15.70	15.80
C	12.70	13.08	14.27
D	4.30	4.50	4.70
E	8.59	9.20	9.40
F	2.54 BSC		
G1	1.32	1.52	1.62
G2	0.70	0.80	0.95
G3	0.45	0.50	0.60
H dia.	3.50	3.60	3.70
I	2.70	2.80	2.90
J	15.70	15.90	16.25
K	2.20	2.40	2.90
L	1.15	1.30	1.40

11. Ordering information

Part Number	TSSiC065S012D
Package	TO-220-2L
	TSSiC065S012D
Unit Quantity	1000 EA
Packing Type	Tube
RoHS	Yes

12. Notes

SiC Schottky diode portfolio: <http://www.thrivesemi.com/>

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